

Resonant Switching Series

Reverse conducting IGBT with monolithic body diode

IHW30N65R5

Data sheet

Industrial Power Control

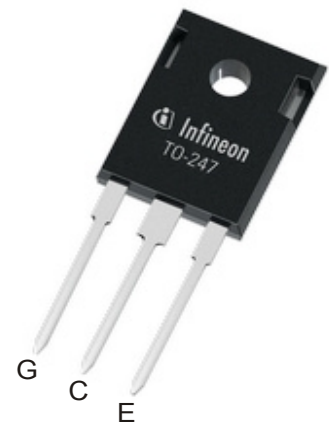
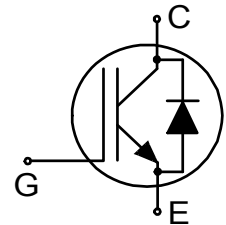
Reverse conducting IGBT with monolithic body diode

Features:

- Powerful monolithic reverse-conducting diode with low forward voltage
- TRENCHSTOP™ technology offers:
 - very tight parameter distribution
 - high ruggedness and stable temperature behavior
 - very low V_{CEsat} and low E_{off}
 - easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Low EMI
- Qualified according to JESD-022 for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Applications:

- Induction cooking
- Inverterized microwave ovens
- Resonant converters



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IHW30N65R5	650V	30A	1.35V	175°C	H30ER5	PG-TO247-3